| | | |
|---|---|---|
| $V_{DM}$ | = | 5200 V |
| $I_{T(AV)M}$ | = | 1800 A |
| $I_{T(RMS)}$ | = | 2830 A |
| $I_{TSM}$ | = | $29 \times 10^3$ A |
| $V_{T0}$ | = | 1.02 V |
| $r_T$ | = | 0.32 mΩ |

# Bi-Directional Control Thyristor

# 5STB 17N5200

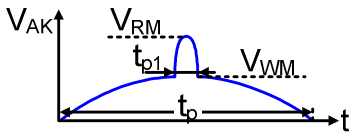
Doc. No. 5SYA1036-04 May 07

- **Two thyristors integrated into one wafer**
- **Patented free-floating silicon technology**
- **Designed for energy management and industrial applications**
- **Optimum power handling capability**
- **Interdigitated amplifying gate**

The electrical and thermal data are valid for one-thyristor-half of the device (unless otherwise stated)

## Blocking

***Maximum rated values*** [1)]

| Parameter | Symbol | Conditions | 5STB 17N5200 | Unit |
|---|---|---|---|---|
| Max. surge peak forward blocking voltage | $V_{SM}$ | $t_p$ = 10 ms, f = 5 Hz<br>$T_{vj}$ = 5…125°C, Note 1 | 5200 | V |
| Max repetitive peak forward blocking voltage | $V_{RM}$ | f = 50 Hz, $t_p$ = 10 ms, $t_{p1}$ = 250 µs,<br>$T_{vj}$ = 5…125°C, Note 1 | 5200 | V |
| Max crest working forward voltages | $V_{WM}$ |  | 2600 | V |
| Critical rate of rise of off-state voltage | $dv/dt_{crit}$ | Exp. to 2950 V, $T_{vj}$ = 125°C | 2000 | V/µs |

***Characteristic values***

| Parameter | Symbol | Conditions | min | typ | max | Unit |
|---|---|---|---|---|---|---|
| Max reverse leakage current | $I_{RM}$ | $V_{RM}$, $T_{vj}$ = 125 °C | | | 400 | mA |

Note 1: Voltage de-rating factor of 0.11% per °C is applicable for Tvj below +5 °C
Note 2: Recommended minimum ratio of $V_{DRM}$ / $V_{DWM}$ or $V_{RRM}$ / $V_{RWM}$ = 2. See App. Note 5SYA 2051.

## Mechanical data

***Maximum rated values*** [1)]

| Parameter | Symbol | Conditions | min | typ | max | Unit |
|---|---|---|---|---|---|---|
| Mounting force | $F_M$ | | 81 | 90 | 108 | kN |
| Acceleration | a | Device unclamped | | | 50 | $m/s^2$ |
| Acceleration | a | Device clamped | | | 100 | $m/s^2$ |

***Characteristic values***

| Parameter | Symbol | Conditions | min | typ | max | Unit |
|---|---|---|---|---|---|---|
| Weight | m | | | | 2.9 | kg |
| Housing thickness | H | $F_M$ = 90 kN, $T_a$ = 25 °C | 34.8 | | 35.4 | mm |
| Surface creepage distance | $D_S$ | | 53 | | | mm |
| Air strike distance | $D_a$ | | 22 | | | mm |

1) Maximum rated values indicate limits beyond which damage to the device may occur

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## On-state

***Maximum rated values*** [1)]

| Parameter | Symbol | Conditions | min | typ | max | Unit |
|---|---|---|---|---|---|---|
| Average on-state current | $I_{T(AV)M}$ | Half sine wave, $T_c$ = 70 °C | | | 1800 | A |
| RMS on-state current | $I_{T(RMS)}$ | | | | 2830 | A |
| RMS on-state current | $I_{T(RMS)}$ | Full sine wave, $T_c$ = 70 °C | | | 4000 | A |
| Peak non-repetitive surge current | $I_{TSM}$ | $t_p$ = 10 ms, $T_{vj}$ = 125 °C, sine wave after surge: $V_D = V_R$= 0 V | | | $29.0\times10^3$ | A |
| Limiting load integral | $I^2t$ | | | | $4.21\times10^6$ | $A^2s$ |
| Peak non-repetitive surge current | $I_{TSM}$ | $t_p$ = 8.3 ms, $T_{vj}$ = 125 °C, sine wave after surge: $V_D = V_R$= 0 V | | | $31.0\times10^3$ | A |
| Limiting load integral | $I^2t$ | | | | $3.99\times10^6$ | $A^2s$ |

***Characteristic values***

| Parameter | Symbol | Conditions | min | typ | max | Unit |
|---|---|---|---|---|---|---|
| On-state voltage | $V_T$ | $I_T$ = 2000 A, $T_{vj}$ = 125 °C | | | 1.68 | V |
| Threshold voltage | $V_{T0}$ | $I_T$ = 1000 A - 3000 A, $T_{vj}$= 125 °C | | | 1.02 | V |
| Slope resistance | $r_T$ | | | | 0.32 | mΩ |
| Holding current | $I_H$ | $T_{vj}$ = 25 °C | 50 | | 250 | mA |
| | | $T_{vj}$ = 125 °C | | | 150 | mA |
| Latching current | $I_L$ | $T_{vj}$ = 25 °C | | | 500 | mA |
| | | $T_{vj}$ = 125 °C | | | 300 | mA |

## Switching

***Maximum rated values*** [1)]

| Parameter | Symbol | Conditions | | min | typ | max | Unit |
|---|---|---|---|---|---|---|---|
| Critical rate of rise of on-state current | $di/dt_{crit}$ | $T_{vj}$ = 125 °C, $I_{TRM}$ = 3000 A, | Cont. f = 50 Hz | | | 250 | A/µs |
| Critical rate of rise of on-state current | $di/dt_{crit}$ | $V_D \leq$ 2950 V, $I_{FG}$ = 2 A, $t_r$ = 0.5 µs | Cont. f = 1Hz | | | 500 | A/µs |
| Circuit commutated turn-off time | $t_q$ | $T_{vj}$ = 125 °C, $I_{TRM}$ = 2000 A, $V_R$ = 200 V, $di_T/dt$ = -1.5 A/µs, $V_D \leq 0.67 \cdot V_{RM}$, $dv_D/dt$ = 20 V/µs, | | 700 | | | µs |
| Critical rate of rise of commutating voltage | $dv/dt_{com}$ | $T_{vj}$ = 125 °C, $V_R \leq 0.67 \cdot V_{RM}$ | | | | 500 | V/µs |

***Characteristic values***

| Parameter | Symbol | Conditions | min | typ | max | Unit |
|---|---|---|---|---|---|---|
| Reverse recovery charge | $Q_{rr}$ | $T_{vj}$ = 125 °C, $I_{TRM}$ = 2000 A, $V_R$ = 200 V, $di_T/dt$ = -1.5 A/µs | 3500 | | 6500 | µAs |
| Reverse recovery current | $I_{RM}$ | | 65 | | 90 | A |
| Gate turn-on delay time | $t_{gd}$ | $T_{vj}$ = 25 °C, $V_D = 0.4 \cdot V_{RM}$, $I_{FG}$ = 2 A, $t_r$ = 0.5 µs | | | 3 | µs |

# Triggering

***Maximum rated values*** [1)]

| Parameter | Symbol | Conditions | min | typ | max | Unit |
|---|---|---|---|---|---|---|
| Peak forward gate voltage | $V_{FGM}$ | | | | 12 | V |
| Max. rated peak forward gate current | $I_{FGM}$ | | | | 10 | A |
| Peak reverse gate voltage | $V_{RGM}$ | | | | 10 | V |
| Max. rated gate power loss | $P_G$ | For DC gate current | | | 3 | W |
| Max. rated peak forward gate power | $P_{GM(AV)}$ | | see Fig. 9 | | | W |

***Characteristic values***

| Parameter | Symbol | Conditions | min | typ | max | Unit |
|---|---|---|---|---|---|---|
| Gate trigger voltage | $V_{GT}$ | $T_{vj}$ = 25 °C | | | 2.6 | V |
| Gate trigger current | $I_{GT}$ | $T_{vj}$ = 25 °C | | | 400 | mA |
| Gate non-trigger voltage | $V_{GD}$ | $V_D$ = 0.4 x $V_{RM}$, $T_{vj}$ = 125 °C | 0.3 | | | V |
| Gate non-trigger current | $I_{GD}$ | $V_D$ = 0.4 x $V_{RM}$ | 10 | | | mA |

# Thermal

***Maximum rated values*** [1)]

| Parameter | Symbol | Conditions | min | typ | max | Unit |
|---|---|---|---|---|---|---|
| Operating junction temperature range | $T_{vj}$ | | | | 125 | °C |
| Storage temperature range | $T_{stg}$ | | -40 | | 140 | °C |

***Characteristic values***

| Parameter | Symbol | Conditions | min | typ | max | Unit |
|---|---|---|---|---|---|---|
| Thermal resistance junction to case | $R_{th(j-c)}$ | Double-side cooled<br>$F_m$ = 81...108 kN | | | 11.4 | K/kW |
| (Valid for one thyristor half no heat flow to the second half.) | $R_{th(j-c)}$ | Single-side cooled<br>$F_m$ = 81...108 kN | | | 22.8 | K/kW |
| Thermal resistance case to heatsink | $R_{th(c-h)}$ | Double-side cooled<br>$F_m$ = 81...108 kN | | | 2 | K/kW |
| | $R_{th(c-h)}$ | Single-side cooled<br>$F_m$ = 81...108 kN | | | 4 | K/kW |

**Analytical function for transient thermal impedance:**

$$Z_{th(j-c)}(t) = \sum_{i=1}^{n} R_i(1 - e^{-t/t_i})$$

| i | 1 | 2 | 3 | 4 |
|---|---|---|---|---|
| $R_i$(K/kW) | 6.770 | 2.510 | 1.340 | 0.780 |
| $\tau_i$(s) | 0.8651 | 0.1558 | 0.0212 | 0.0075 |

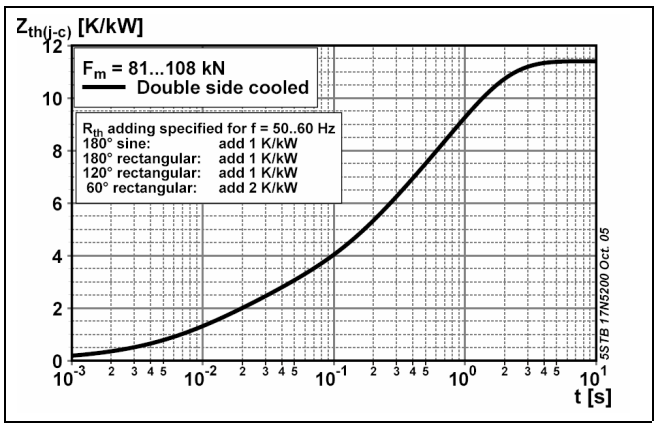


**Fig. 1** Transient thermal impedance (junction-to-case) vs. time

**On-state characteristic model:**

$$V_{T\max} = A + B \cdot I_T + C \cdot \ln(I_T + 1) + D \cdot \sqrt{I_T}$$

Valid for $i_T$ = 500 – 4000 A

| A | B | C | D |
|---|---|---|---|
| 1.309 | $80.0\times10^{-6}$ | $-125.0\times10^{-3}$ | $26.0\times10^{-3}$ |

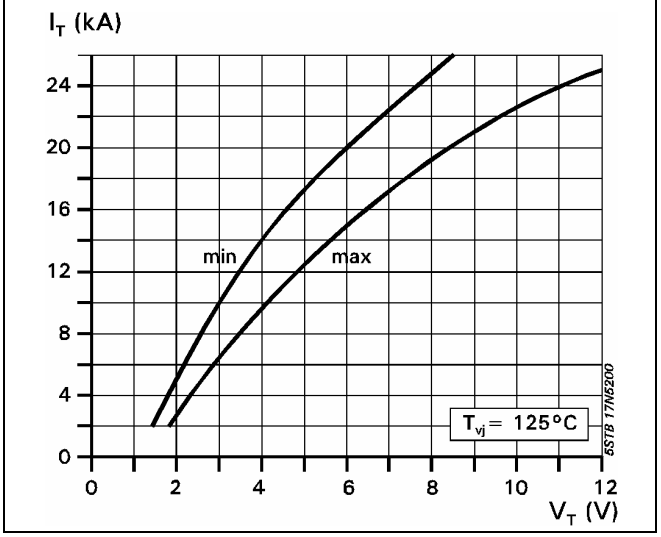


**Fig. 2** On-state characteristics, $T_j$ = 125°C, 10ms half sine

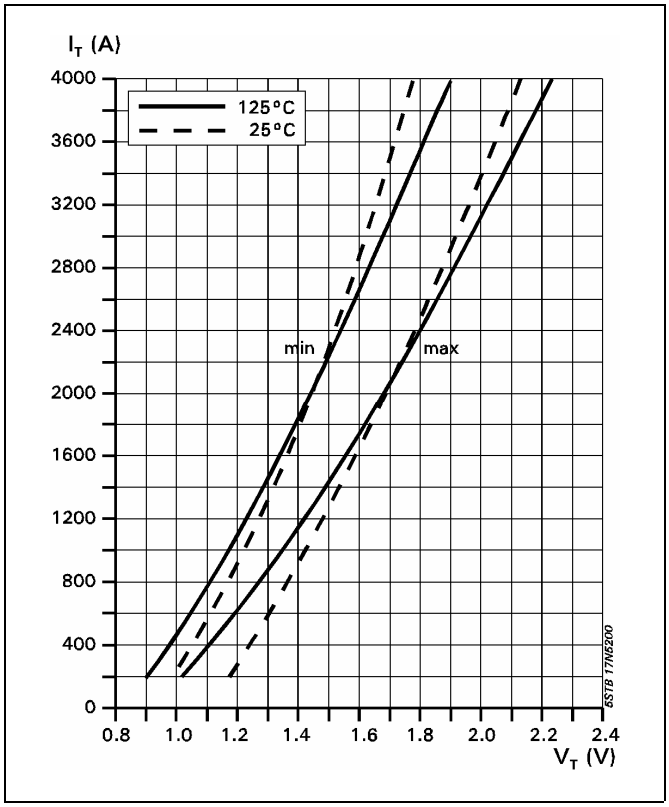


**Fig. 3** On-state voltage characteristics

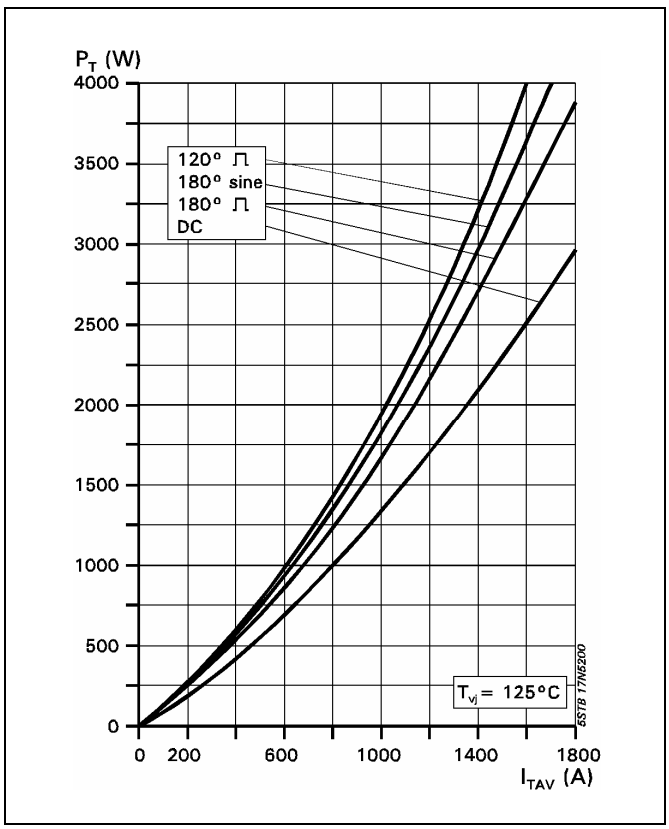


**Fig. 4** On-state power dissipation vs. mean on-state current. Turn-on losses excluded.

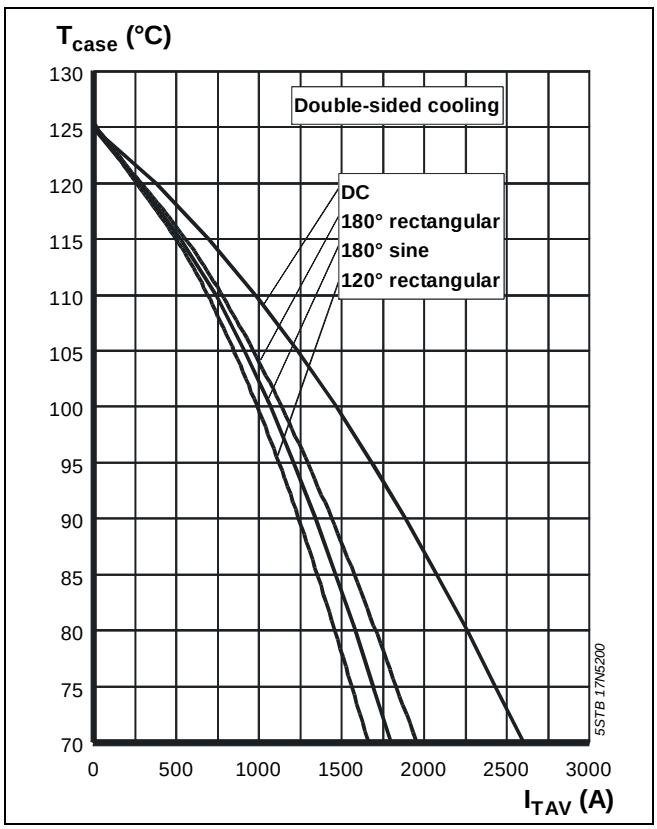


**Fig. 5** Max. permissible case temperature vs. mean on-state current. Switching losses ignored.

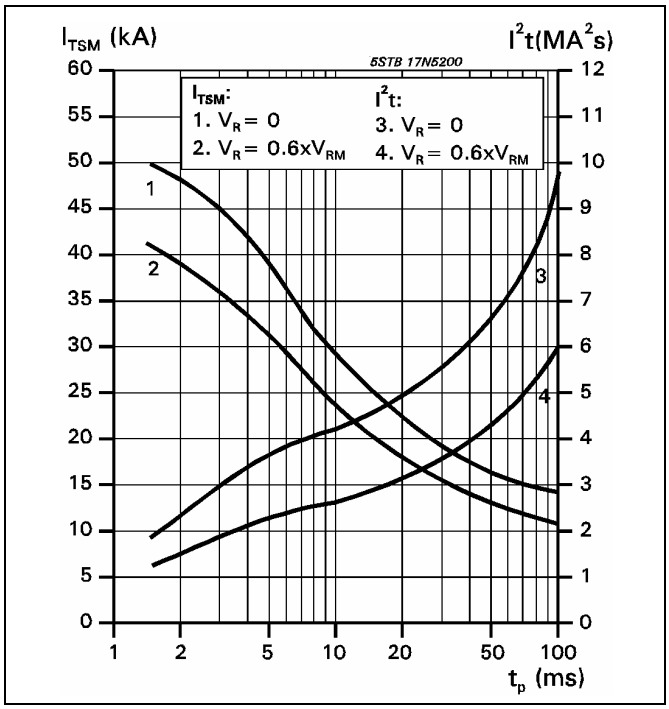


**Fig. 6** Surge on-state current vs. pulse length. Half-sine wave.

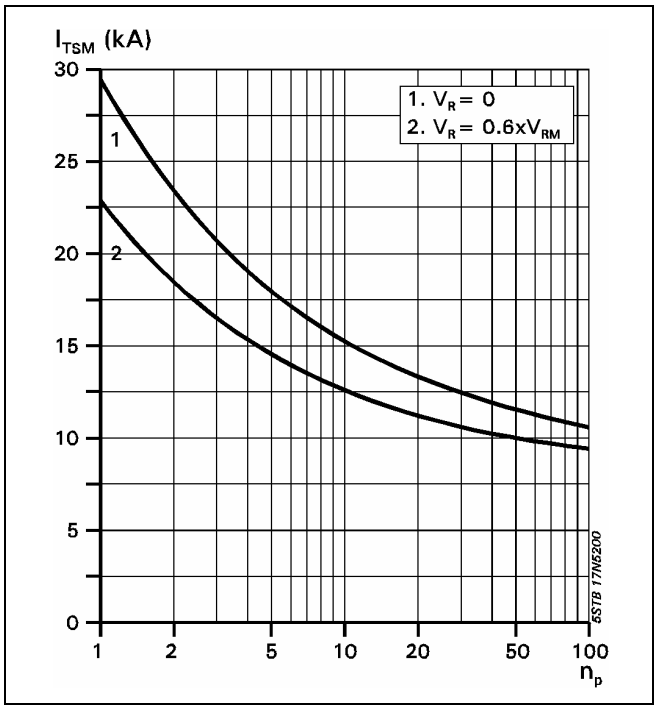


**Fig. 7** Surge on-state current vs. number of pulses. Half-sine wave, 10 ms, 50Hz.

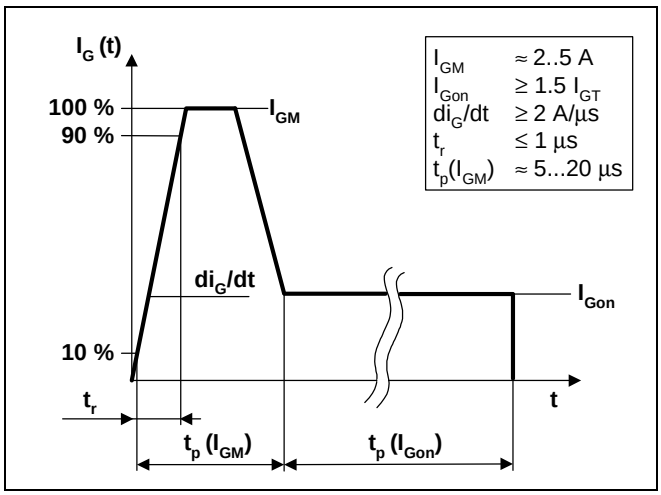


**Fig. 8** Recommended gate current waveform

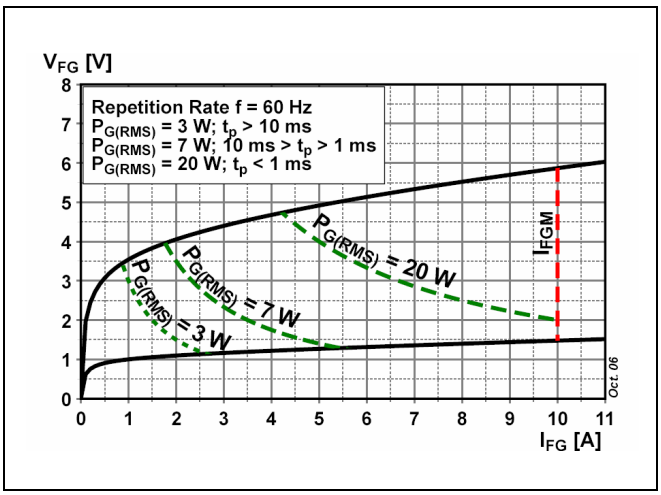


**Fig. 9** Max. peak gate power loss

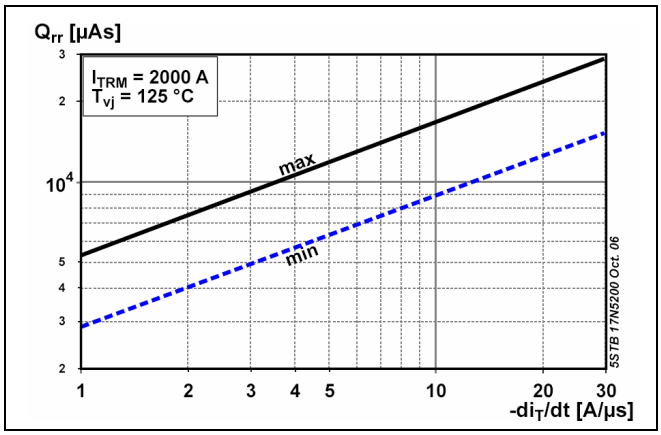


**Fig. 10** Reverse recovery charge vs. decay rate of on-state current

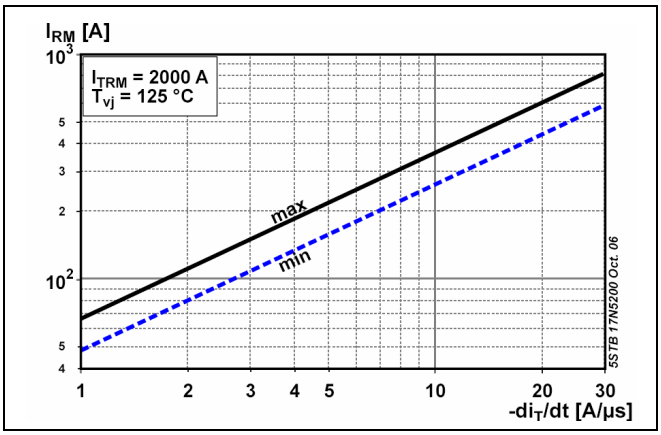


**Fig. 11** Peak reverse recovery current vs. decay rate of on-state current

# Turn-on and Turn-off losses

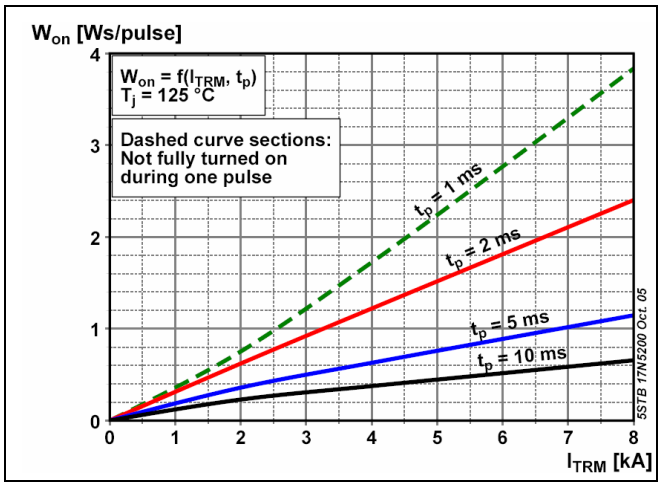


**Fig. 12** Turn-on energy, half sinusoidal waves

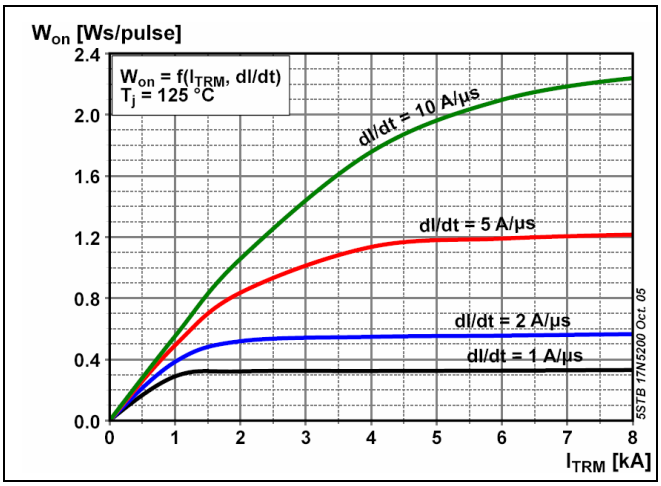


**Fig. 13** Turn-on energy, rectangular waves

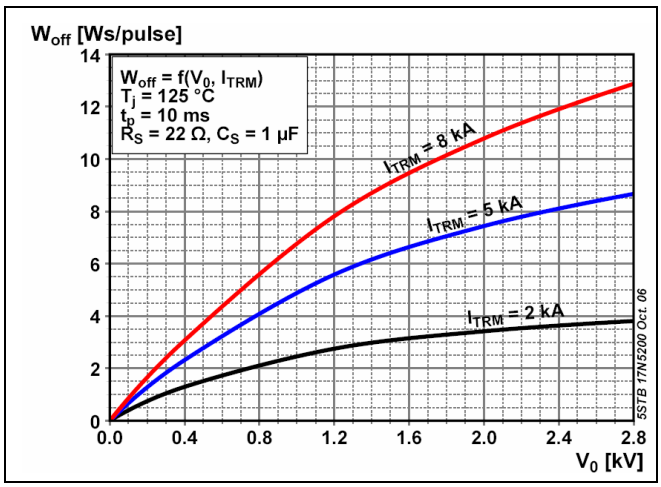


**Fig. 14** Turn-off energy, half sinusoidal waves

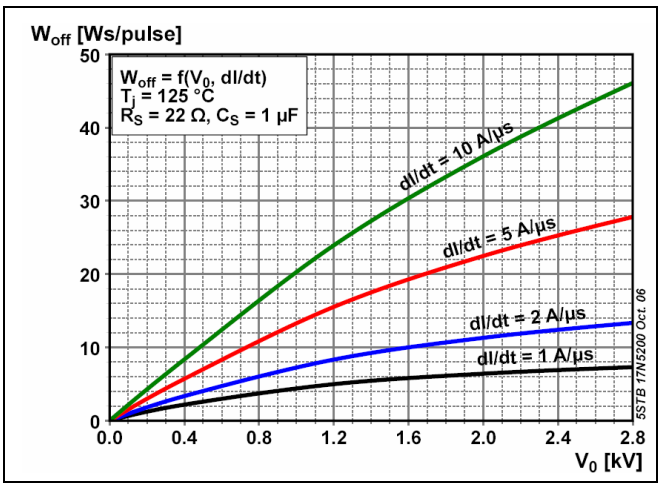


**Fig. 15** Turn-off energy, rectangular waves

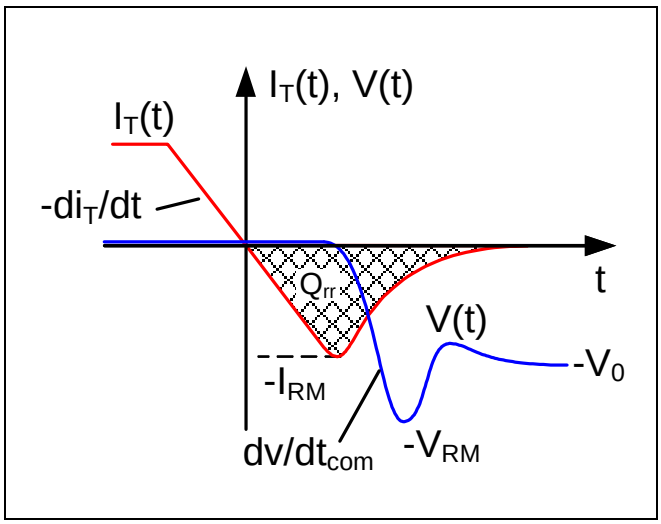


**Fig. 16** Current and voltage waveforms at turn-off

**Total power loss for repetitive waveforms:**

$$P_{TOT} = P_T + W_{on} \cdot f + W_{off} \cdot f$$

where

$$P_T = \frac{1}{T}\int_0^T I_T \cdot V_T(I_T)\ dt$$

**Fig. 17** Relationships for power loss

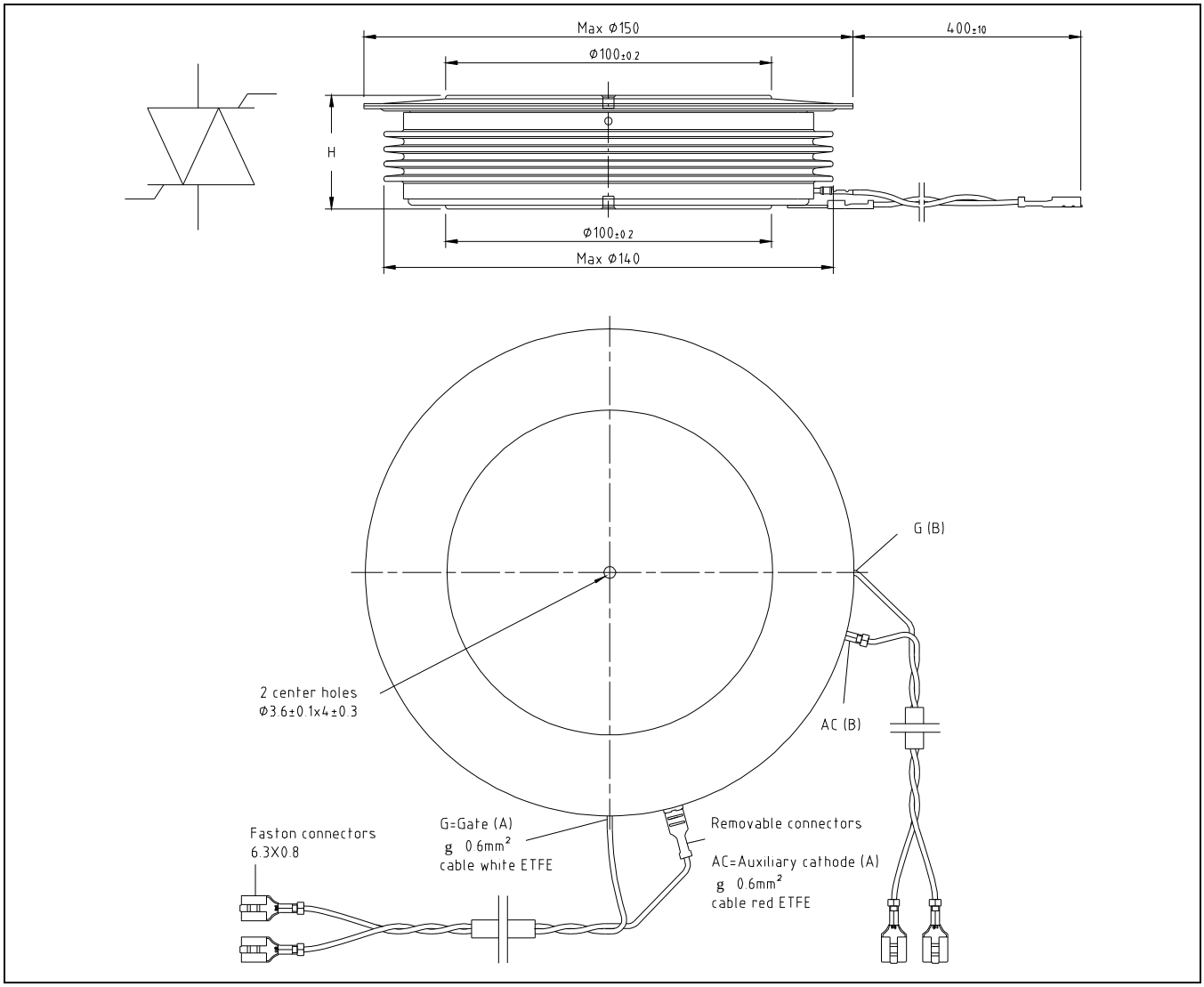


**Fig. 18** Device Outline Drawing

## Related documents:

| | |
|---|---|
| 5SYA 2020 | Design of RC-Snubber for Phase Control Applications |
| 5SYA 2049 | Voltage definitions for phase control thyristors and diodes |
| 5SYA 2051 | Voltage ratings of high power semiconductors |
| 5SYA 2034 | Gate-Drive Recommendations for PCT's |
| 5SYA 2036 | Recommendations regarding mechanical clamping of Press Pack High Power Semiconductors |
| 5SZK 9104 | Specification of environmental class for pressure contact diodes, PCTs and GTO, STORAGE available on request, please contact factory |
| 5SZK 9105 | Specification of environmental class for pressure contact diodes, PCTs and GTO, TRANSPORTATION available on request, please contact factory |

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Doc. No. 5SYA1036-04 May 07